

# 2–10 GHz Medium Power Gallium Arsenide FET

## Technical Data

**ATF-46171**

### Features

- **High Output Power:**  
27.0 dBm Typical  $P_{1\text{dB}}$  at 4 GHz
- **High Gain at 1 dB Compression:**  
11.0 dB Typical  $G_{1\text{dB}}$  at 4 GHz
- **High Power Efficiency:**  
38% Typical at 4 GHz
- **Hermetic Metal-Ceramic Stripline Package**

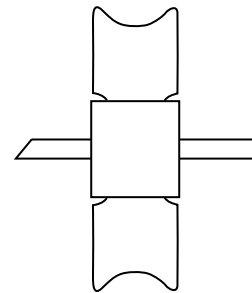
### Description

The ATF-46171 is a gallium arsenide Schottky-barrier-gate field effect transistor designed for medium power, linear amplification in the 2 to 10 GHz frequency

range. This nominally 0.5 micron gate length GaAs FET is an interdigitated four-cell structure using airbridge interconnects between drain fingers. Total gate periphery is 1.25 millimeters. Proven gold based metallization systems and nitride passivation assure a rugged, reliable device.

This device is suitable for applications in space, airborne, military ground and shipboard, and commercial environments. It is supplied in a hermetic high reliability package with low parasitic reactance and minimum thermal resistance.

### 70 mil Flange Package



### Electrical Specifications, $T_A = 25^\circ\text{C}$

Symbol	Parameters and Test Conditions	Units	Min.	Typ.	Max.
$P_{1\text{dB}}$	Power Output @ 1 dB Gain Compression: $V_{\text{DS}} = 9\text{ V}, I_{\text{DS}} = 125\text{ mA}$	f = 4.0 GHz dBm	25.0	27.0	
$G_{1\text{dB}}$	1 dB Compressed Gain: $V_{\text{DS}} = 9\text{ V}, I_{\text{DS}} = 125\text{ mA}$	f = 4.0 GHz dB	10.0	11.0	
$\eta_{\text{add}}$	Efficiency @ $P_{1\text{dB}}$ : $V_{\text{DS}} = 9\text{ V}, I_{\text{DS}} = 125\text{ mA}$	f = 4.0 GHz %		38	
$g_m$	Transconductance: $V_{\text{DS}} = 2.5\text{ V}, I_{\text{DS}} = 125\text{ mA}$	mmho		100	
$I_{\text{DSS}}$	Saturated Drain Current: $V_{\text{DS}} = 2.5\text{ V}, V_{\text{GS}} = 0\text{ V}$	mA	200	330	450
$V_P$	Pinch-off Voltage: $V_{\text{DS}} = 2.5\text{ V}, I_{\text{DS}} = 5\text{ mA}$	V	-5.4	-3.5	-2.0

## ATF-46171 Absolute Maximum Ratings

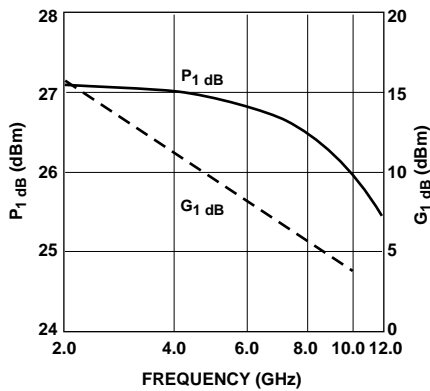
Symbol	Parameter	Units	Absolute Maximum <sup>[1]</sup>
$V_{DS}$	Drain-Source Voltage	V	+14
$V_{GS}$	Gate-Source Voltage	V	-7
$V_{GD}$	Gate-Drain Voltage	V	-16
$I_{DS}$	Drain Current	mA	$I_{DSS}$
$P_T$	Power Dissipation <sup>[2,3]</sup>	W	2.0
$T_{CH}$	Channel Temperature	°C	175
$T_{STG}$	Storage Temperature	°C	-65 to +175

**Thermal Resistance:**  $\theta_{jc} = 75^\circ\text{C/W}; T_{CH} = 150^\circ\text{C}$   
**Liquid Crystal Measurement:** 1  $\mu\text{m}$  Spot Size<sup>[4]</sup>

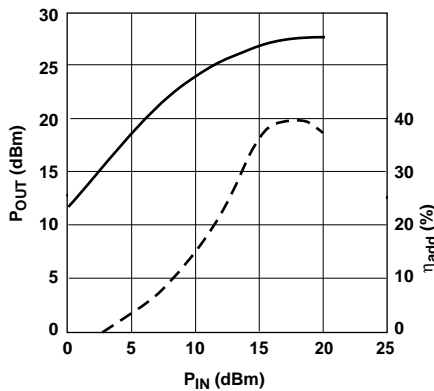
### Notes:

1. Permanent damage may occur if any of these limits are exceeded.
2.  $T_{CASE\ TEMPERATURE} = 25^\circ\text{C}$ .
3. Derate at 13 mW/°C for  $T_{CASE} > 25^\circ\text{C}$ .
4. The small spot size of this technique results in a higher, though more accurate determination of  $\theta_{jc}$  than do alternate methods. See MEASUREMENTS section for more information.

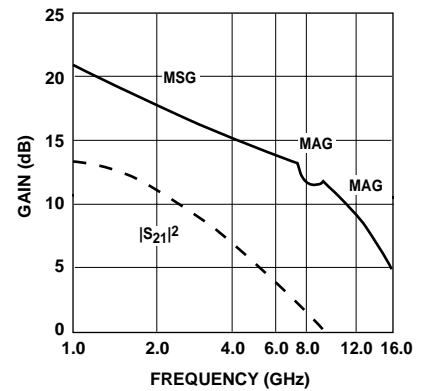
## ATF-46171 Typical Performance, $T_A = 25^\circ\text{C}$



**Figure 1. Power Output @ 1 dB Gain Compression and 1 dB Compressed Gain vs. Frequency.**  
 $V_{DS} = 9\text{V}, I_{DS} = 125\text{ mA}$ .



**Figure 2. Output Power and Power Added Efficiency vs. Input Power.**  
 $V_{DS} = 9\text{ V}, I_{DS} = 125\text{ mA}, f = 4.0\text{ GHz}$ .



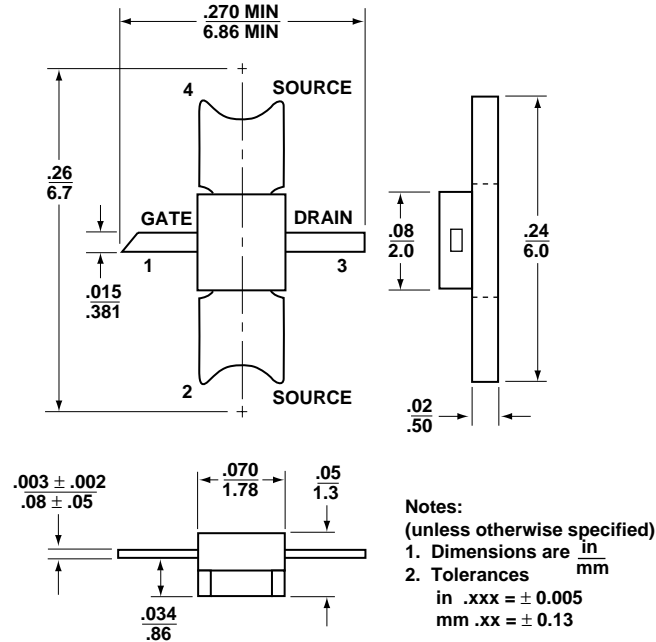
**Figure 3. Insertion Power Gain, Maximum Available Gain and Maximum Stable Gain vs. Frequency.**  
 $V_{DS} = 9\text{ V}, I_{DS} = 125\text{ mA}$ .

**Typical Scattering Parameters, Common Emitter,  $Z_0 = 50 \Omega$ ,  $T_A = 25^\circ\text{C}$ ,  $V_{DS} = 9\text{V}$ ,  $I_{DS} = 125\text{mA}$**

Freq. GHz	$S_{11}$		$S_{21}$			$S_{12}$			$S_{22}$	
	Mag.	Ang.	dB	Mag.	Ang.	dB	Mag.	Ang.	Mag.	Ang.
1.0	.95	-54	12.7	4.30	138	-29.4	.034	63	.71	-22
2.0	.84	-106	11.0	3.56	99	-26.7	.046	30	.60	-44
3.0	.81	-145	8.9	2.80	67	-25.7	.052	13	.52	-71
4.0	.81	-172	6.6	2.14	40	-25.0	.056	2	.52	-101
5.0	.80	171	4.6	1.70	18	-24.4	.060	-3	.58	-122
6.0	.79	159	3.1	1.44	1	-24.0	.063	-6	.63	-135
7.0	.78	141	2.2	1.29	-18	-23.5	.067	-10	.63	-147
8.0	.77	123	1.4	1.17	-36	-23.0	.071	-14	.64	-164
9.0	.79	108	-0.1	.99	-58	-22.5	.075	-17	.67	171
10.0	.79	100	-1.4	.85	-73	-22.0	.079	-21	.74	152
11.0	.78	93	-2.5	.75	-86	-21.6	.083	-24	.76	142
12.0	.76	85	-3.5	.67	-97	-20.6	.093	-32	.79	133
13.0	.73	67	-4.3	.61	-118	-19.5	.106	-49	.80	119
14.0	.71	47	-5.8	.51	-138	-19.0	.112	-66	.83	98
15.0	.73	35	-7.5	.42	-157	-18.6	.118	-71	.85	83
16.0	.75	26	-8.9	.36	-157	-18.3	.121	-78	.90	72

A model for this device is available in the DEVICE MODELS section.

**70 mil Flange Package**



Package marking code is 461